

INFORMATION DISCLOSURE CITATION
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ATTY. DOCKET NO.

Serie 6070

SERIAL NO.

Not yet assigned

10/553573

APPLICANT(S)

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FILING DATE

Herewith

GROUP

Unknown

U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date
	A1	US 2001 024867	09/27/2001	Saida et al.			
	A2	US 2001 048973	12/06/2001	Sato et al.			

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	B1	EP 1 441 042	07/28/2004	Europe				
	B2	GB 1 006 803	10/06/1965	United Kingdom				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

C1		International Search Report for PCT/IB04/001346
C2		Smirnova T. P., et al.: "SiCN alloys obtained by remote plasma chemical vapour deposition from novel precursors", Preparation and Characterization, Elsevier Sequoia, NL, vol. 429, no. 1-2, April 1, 2003, pp. 144-151
C3		Grow, J. M., et al., "Growth kinetics and characterization of low pressure chemically vapor deposited Si ₃ N ₄ films from (C ₄ H ₉) ₂ SiH ₂ and NH ₃ ", Materials Letters, vol. 23, 1995, pp. 187-193
C4		Levy, R. A., et al., "Low pressure chemical vapor deposition of silicon nitride using the environmentally friendly tris(dimethylamino)silane precursor", M. Mater. Res., vol. 11, no. 6, June 1996, pp. 1483-1488

Examiner

/Elizabeth Burkhart/

Date Considered

12/31/2008

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